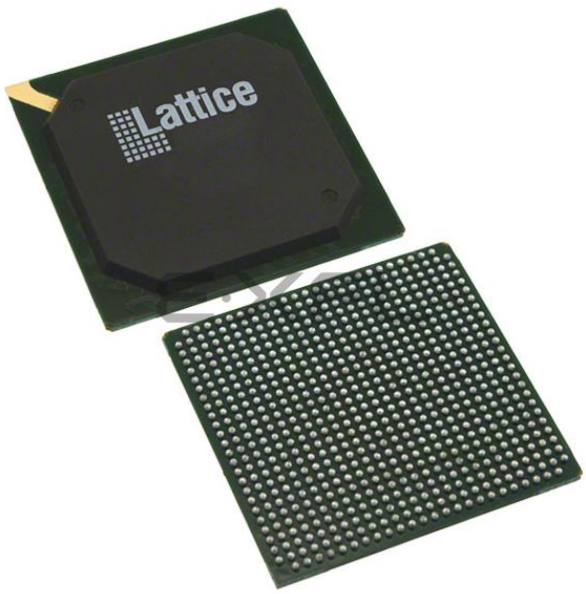


Welcome to E-XFL.COM

Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

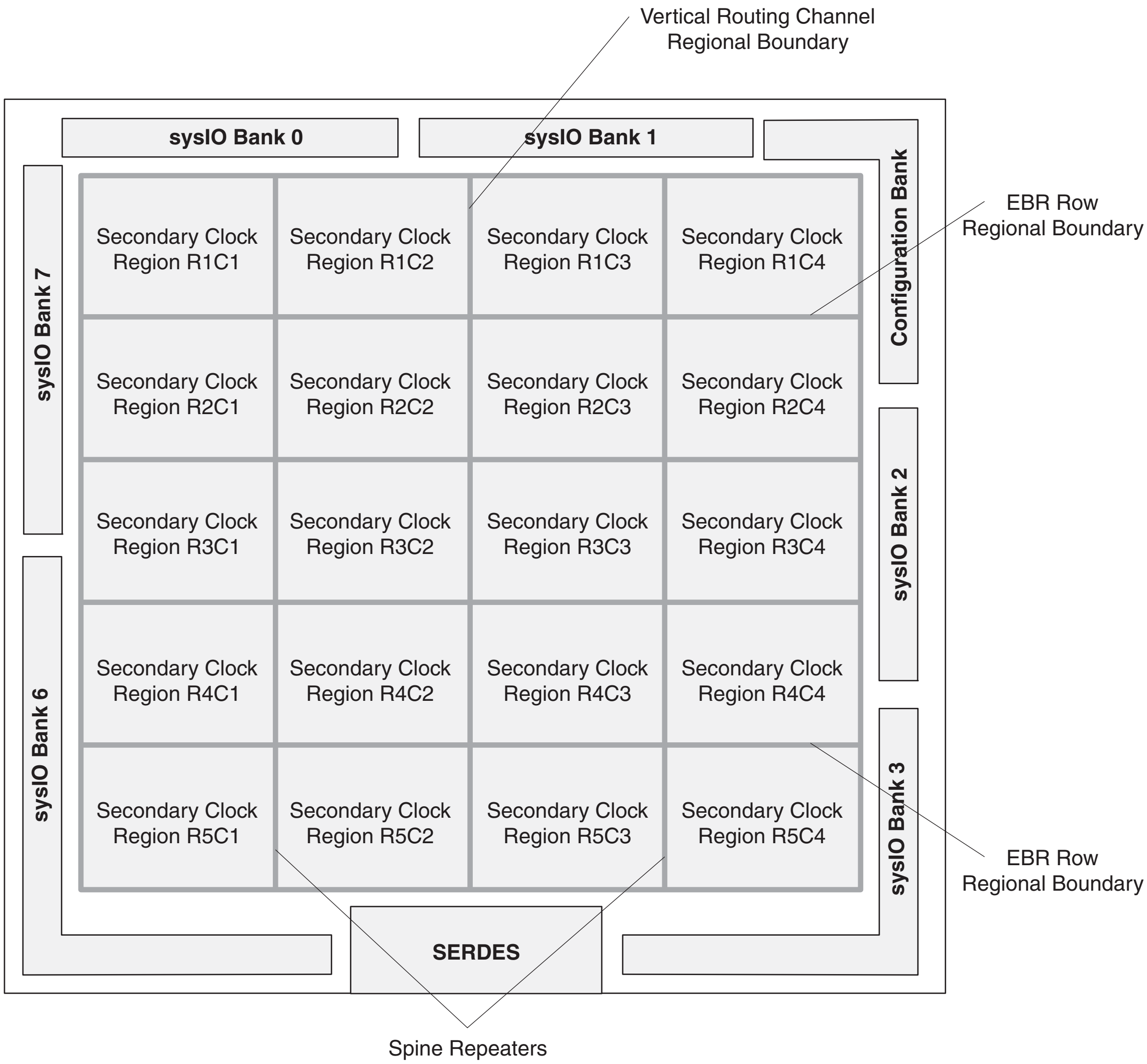
The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Not For New Designs
Number of LABs/CLBs	11500
Number of Logic Elements/Cells	92000
Total RAM Bits	4526080
Number of I/O	380
Number of Gates	-
Voltage - Supply	1.14V ~ 1.26V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	672-BBGA
Supplier Device Package	672-FPBGA (27x27)
Purchase URL	https://www.e-xfl.com/product-detail/lattice-semiconductor/lfe3-95ea-9fn672i

Table 2-6. Secondary Clock Regions

Device	Number of Secondary Clock Regions
ECP3-17	16
ECP3-35	16
ECP3-70	20
ECP3-95	20
ECP3-150	36

Figure 2-15. LatticeECP3-70 and LatticeECP3-95 Secondary Clock Regions



Single, Dual and Pseudo-Dual Port Modes

In all the sysMEM RAM modes the input data and address for the ports are registered at the input of the memory array. The output data of the memory is optionally registered at the output.

EBR memory supports the following forms of write behavior for single port or dual port operation:

1. **Normal** – Data on the output appears only during a read cycle. During a write cycle, the data (at the current address) does not appear on the output. This mode is supported for all data widths.

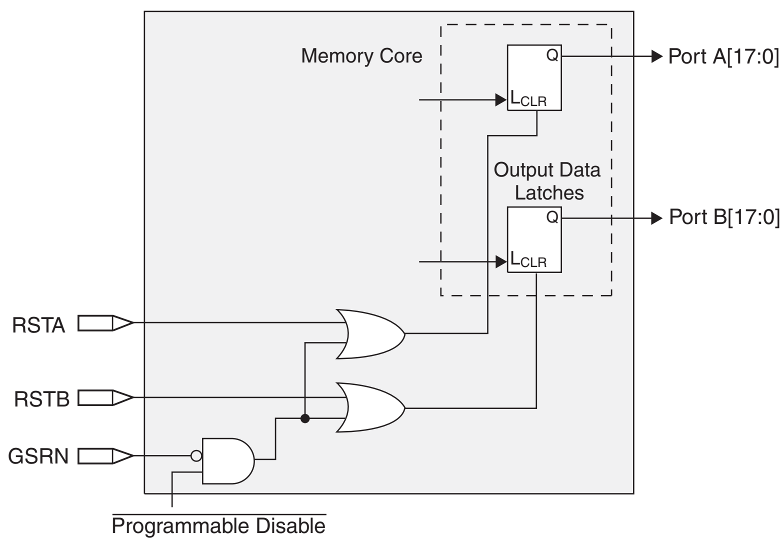
2. **Write Through** – A copy of the input data appears at the output of the same port during a write cycle. This mode is supported for all data widths.

3. **Read-Before-Write (EA devices only)** – When new data is written, the old content of the address appears at the output. This mode is supported for x9, x18, and x36 data widths.

Memory Core Reset

The memory array in the EBR utilizes latches at the A and B output ports. These latches can be reset asynchronously or synchronously. RSTA and RSTB are local signals, which reset the output latches associated with Port A and Port B, respectively. The Global Reset (GSRN) signal can reset both ports. The output data latches and associated resets for both ports are as shown in Figure 2-22.

Figure 2-22. Memory Core Reset



For further information on the sysMEM EBR block, please see the list of technical documentation at the end of this data sheet.

sysDSP™ Slice

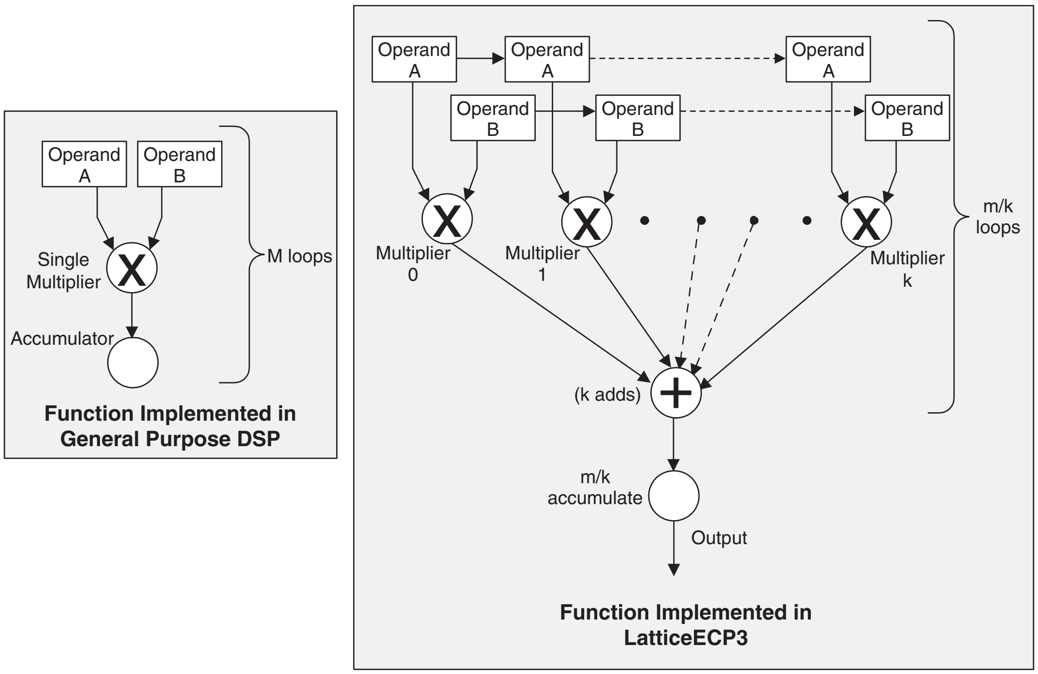
The LatticeECP3 family provides an enhanced sysDSP architecture, making it ideally suited for low-cost, high-performance Digital Signal Processing (DSP) applications. Typical functions used in these applications are Finite Impulse Response (FIR) filters, Fast Fourier Transforms (FFT) functions, Correlators, Reed-Solomon/Turbo/Convolution encoders and decoders. These complex signal processing functions use similar building blocks such as multiply-adders and multiply-accumulators.

sysDSP Slice Approach Compared to General DSP

Conventional general-purpose DSP chips typically contain one to four (Multiply and Accumulate) MAC units with fixed data-width multipliers; this leads to limited parallelism and limited throughput. Their throughput is increased by higher clock speeds. The LatticeECP3, on the other hand, has many DSP slices that support different data widths.

This allows designers to use highly parallel implementations of DSP functions. Designers can optimize DSP performance vs. area by choosing appropriate levels of parallelism. Figure 2-23 compares the fully serial implementation to the mixed parallel and serial implementation.

Figure 2-23. Comparison of General DSP and LatticeECP3 Approaches



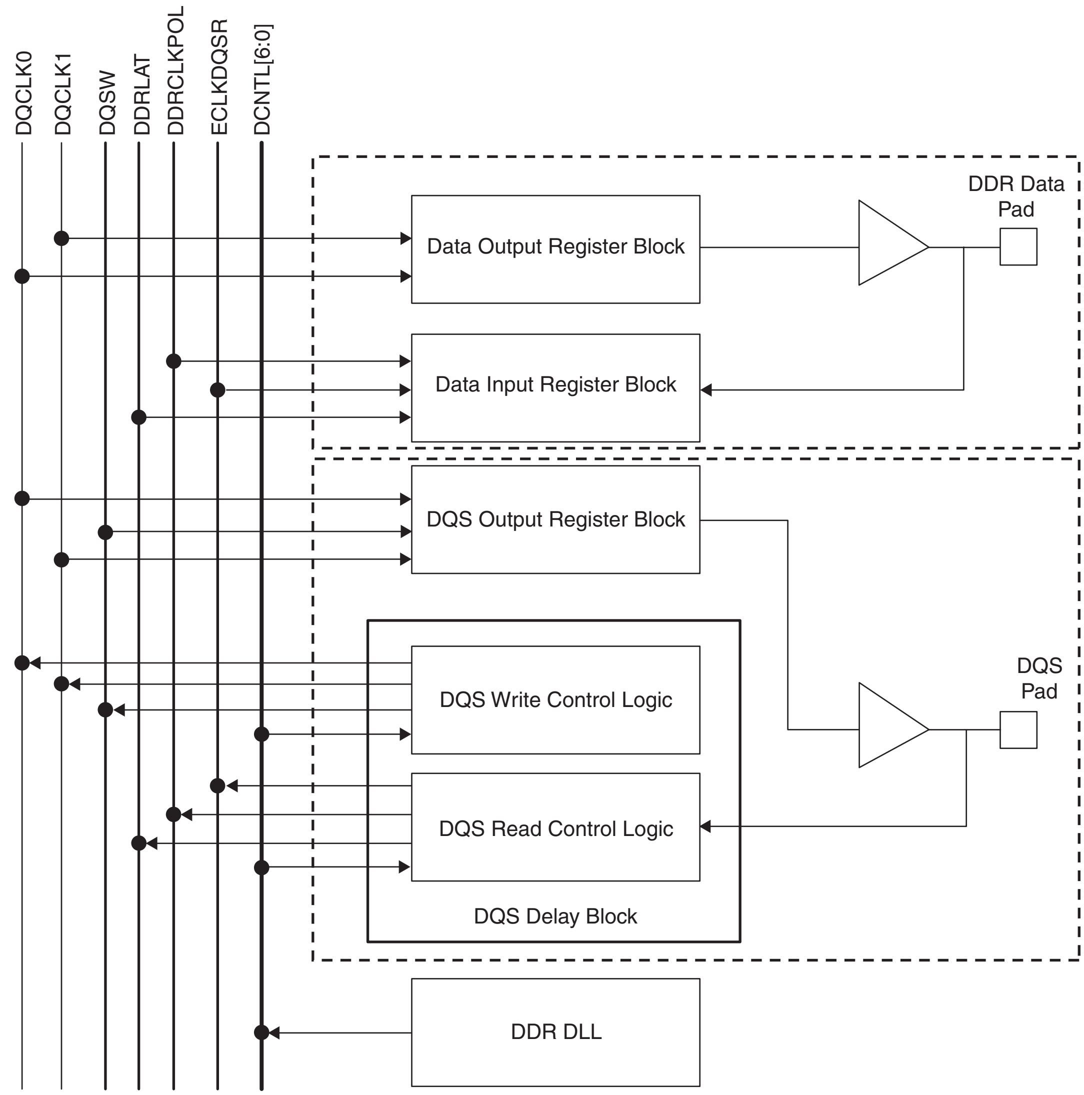
LatticeECP3 sysDSP Slice Architecture Features

The LatticeECP3 sysDSP Slice has been significantly enhanced to provide functions needed for advanced processing applications. These enhancements provide improved flexibility and resource utilization.

The LatticeECP3 sysDSP Slice supports many functions that include the following:

- Multiply (one 18 x 36, two 18 x 18 or four 9 x 9 Multiplies per Slice)
- Multiply (36 x 36 by cascading across two sysDSP slices)
- Multiply Accumulate (up to 18 x 36 Multipliers feeding an Accumulator that can have up to 54-bit resolution)
- Two Multiplies feeding one Accumulate per cycle for increased processing with lower latency (two 18 x 18 Multiplies feed into an accumulator that can accumulate up to 52 bits)
- Flexible saturation and rounding options to satisfy a diverse set of applications situations
- Flexible cascading across DSP slices
  - — Minimizes fabric use for common DSP and ALU functions
  - — Enables implementation of FIR Filter or similar structures using dedicated sysDSP slice resources only
  - — Provides matching pipeline registers
  - — Can be configured to continue cascading from one row of sysDSP slices to another for longer cascade chains
- Flexible and Powerful Arithmetic Logic Unit (ALU) Supports:
  - — Dynamically selectable ALU OPCODE
  - — Ternary arithmetic (addition/subtraction of three inputs)
  - — Bit-wise two-input logic operations (AND, OR, NAND, NOR, XOR and XNOR)
  - — Eight flexible and programmable ALU flags that can be used for multiple pattern detection scenarios, such

Figure 2-37. DQS Local Bus



Polarity Control Logic

In a typical DDR Memory interface design, the phase relationship between the incoming delayed DQS strobe and the internal system clock (during the READ cycle) is unknown. The LatticeECP3 family contains dedicated circuits to transfer data between these domains. A clock polarity selector is used to prevent set-up and hold violations at the domain transfer between DQS (delayed) and the system clock. This changes the edge on which the data is registered in the synchronizing registers in the input register block. This requires evaluation at the start of each READ cycle for the correct clock polarity.

Prior to the READ operation in DDR memories, DQS is in tristate (pulled by termination). The DDR memory device drives DQS low at the start of the preamble state. A dedicated circuit detects the first DQS rising edge after the preamble state. This signal is used to control the polarity of the clock to the synchronizing registers.

DDR3 Memory Support

LatticeECP3 supports the read and write leveling required for DDR3 memory interfaces.

Read leveling is supported by the use of the DDRCLKPOL and the DDRLAT signals generated in the DQS Read Control logic block. These signals dynamically control the capture of the data with respect to the DQS at the input register block.

2. **Left and Right (Banks 2, 3, 6 and 7) sysI/O Buffer Pairs (50% Differential and 100% Single-Ended Outputs)**
   The sysI/O buffer pairs in the left and right banks of the device consist of two single-ended output drivers, two sets of single-ended input buffers (both ratioed and referenced) and one differential output driver. One of the referenced input buffers can also be configured as a differential input. In these banks the two pads in the pair are described as "true" and "comp", where the true pad is associated with the positive side of the differential I/O, and the comp (complementary) pad is associated with the negative side of the differential I/O.

   In addition, programmable on-chip input termination (parallel or differential, static or dynamic) is supported on these sides, which is required for DDR3 interface. However, there is no support for hot-socketing for the I/O pins located on the left and right side of the device as the PCI clamp is always enabled on these pins.

   LVDS, RSDS, PPLVDS and Mini-LVDS differential output drivers are available on 50% of the buffer pairs on the left and right banks.

3. **Configuration Bank sysI/O Buffer Pairs (Single-Ended Outputs, Only on Shared Pins When Not Used by Configuration)**
   The sysI/O buffers in the Configuration Bank consist of ratioed single-ended output drivers and single-ended input buffers. This bank does not support PCI clamp like the other banks on the top, left, and right sides.

   The two pads in the pair are described as "true" and "comp", where the true pad is associated with the positive side of the differential input buffer and the comp (complementary) pad is associated with the negative side of the differential input buffer.

Programmable PCI clamps are only available on the top banks. PCI clamps are used primarily on inputs and bi-directional pads to reduce ringing on the receiving end.

Typical sysI/O I/O Behavior During Power-up

The internal power-on-reset (POR) signal is deactivated when V_{CC}, V_{CCIO8} and V_{CCAUX} have reached satisfactory levels. After the POR signal is deactivated, the FPGA core logic becomes active. It is the user's responsibility to ensure that all other V_{CCIO} banks are active with valid input logic levels to properly control the output logic states of all the I/O banks that are critical to the application. For more information about controlling the output logic state with valid input logic levels during power-up in LatticeECP3 devices, see the list of technical documentation at the end of this data sheet.

The V_{CC} and V_{CCAUX} supply the power to the FPGA core fabric, whereas the V_{CCIO} supplies power to the I/O buffers. In order to simplify system design while providing consistent and predictable I/O behavior, it is recommended that the I/O buffers be powered-up prior to the FPGA core fabric. V_{CCIO} supplies should be powered-up before or together with the V_{CC} and V_{CCAUX} supplies.

Supported sysI/O Standards

The LatticeECP3 sysI/O buffer supports both single-ended and differential standards. Single-ended standards can be further subdivided into LVCMOS, LVTTL and other standards. The buffers support the LVTTL, LVCMOS 1.2 V, 1.5 V, 1.8 V, 2.5 V and 3.3 V standards. In the LVCMOS and LVTTL modes, the buffer has individual configuration options for drive strength, slew rates, bus maintenance (weak pull-up, weak pull-down, or a bus-keeper latch) and open drain. Other single-ended standards supported include SSTL and HSTL. Differential standards supported include LVDS, BLVDS, LVPECL, MLVDS, RSDS, Mini-LVDS, PPLVDS (point-to-point LVDS), TRLVDS (Transition Reduced LVDS), differential SSTL and differential HSTL. For further information on utilizing the sysI/O buffer to support a variety of standards please see TN1177, LatticeECP3 sysIO Usage Guide.

There are some restrictions to be aware of when using spread spectrum. When a quad shares a PCI Express x1 channel with a non-PCI Express channel, ensure that the reference clock for the quad is compatible with all protocols within the quad. For example, a PCI Express spread spectrum reference clock is not compatible with most Gigabit Ethernet applications because of tight CTC ppm requirements.

While the LatticeECP3 architecture will allow the mixing of a PCI Express channel and a Gigabit Ethernet, Serial RapidIO or SGMII channel within the same quad, using a PCI Express spread spectrum clocking as the transmit reference clock will cause a violation of the Gigabit Ethernet, Serial RapidIO and SGMII transmit jitter specifications.

For further information on SERDES, please see TN1176, LatticeECP3 SERDES/PCS Usage Guide.

IEEE 1149.1-Compliant Boundary Scan Testability

All LatticeECP3 devices have boundary scan cells that are accessed through an IEEE 1149.1 compliant Test Access Port (TAP). This allows functional testing of the circuit board on which the device is mounted through a serial scan path that can access all critical logic nodes. Internal registers are linked internally, allowing test data to be shifted in and loaded directly onto test nodes, or test data to be captured and shifted out for verification. The test access port consists of dedicated I/Os: TDI, TDO, TCK and TMS. The test access port has its own supply voltage V_{CCJ} and can operate with LVCMOS3.3, 2.5, 1.8, 1.5 and 1.2 standards.

For more information, please see TN1169, LatticeECP3 sysCONFIG Usage Guide.

Device Configuration

All LatticeECP3 devices contain two ports that can be used for device configuration. The Test Access Port (TAP), which supports bit-wide configuration, and the sysCONFIG port, support dual-byte, byte and serial configuration. The TAP supports both the IEEE Standard 1149.1 Boundary Scan specification and the IEEE Standard 1532 In-System Configuration specification. The sysCONFIG port includes seven I/Os used as dedicated pins with the remaining pins used as dual-use pins. See TN1169, LatticeECP3 sysCONFIG Usage Guide for more information about using the dual-use pins as general purpose I/Os.

There are various ways to configure a LatticeECP3 device:

1. JTAG
2. Standard Serial Peripheral Interface (SPI and SPIm modes) - interface to boot PROM memory
3. System microprocessor to drive a x8 CPU port (PCM mode)
4. System microprocessor to drive a serial slave SPI port (SSPI mode)
5. Generic byte wide flash with a MachXO™ device, providing control and addressing

On power-up, the FPGA SRAM is ready to be configured using the selected sysCONFIG port. Once a configuration port is selected, it will remain active throughout that configuration cycle. The IEEE 1149.1 port can be activated any time after power-up by sending the appropriate command through the TAP port.

LatticeECP3 devices also support the Slave SPI Interface. In this mode, the FPGA behaves like a SPI Flash device (slave mode) with the SPI port of the FPGA to perform read-write operations.

BLVDS25

The LatticeECP3 devices support the BLVDS standard. This standard is emulated using complementary LVCMOS outputs in conjunction with a parallel external resistor across the driver outputs. BLVDS is intended for use when multi-drop and bi-directional multi-point differential signaling is required. The scheme shown in Figure 3-2 is one possible solution for bi-directional multi-point differential signals.

Figure 3-2. BLVDS25 Multi-point Output Example

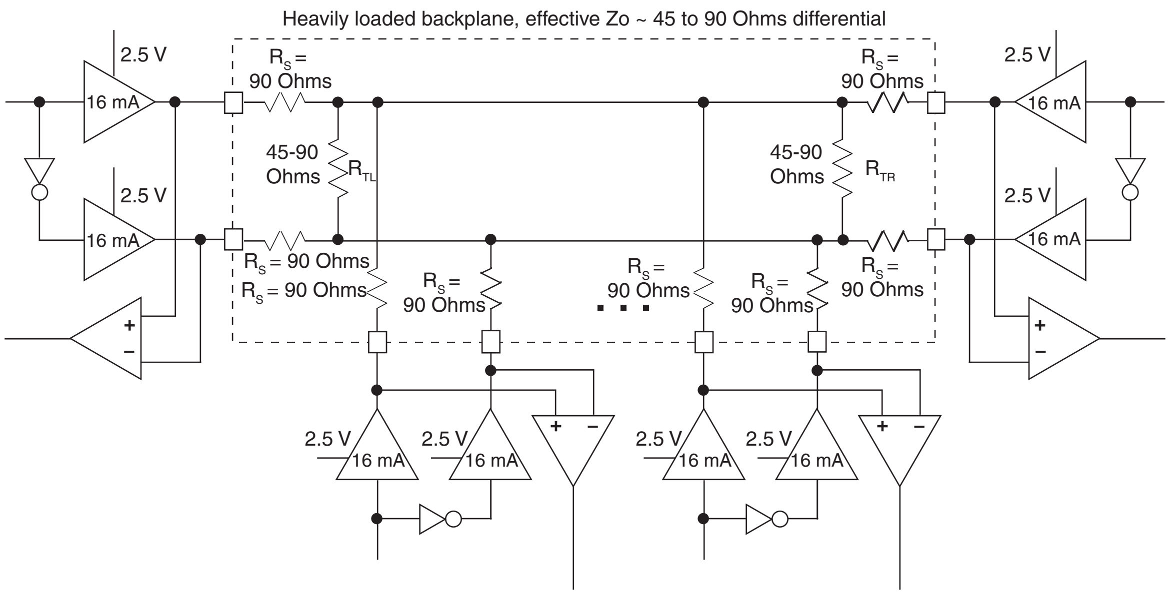


Table 3-2. BLVDS25 DC Conditions[1]

Over Recommended Operating Conditions

Parameter	Description	Typical		Units
		Zo = 45Ω	Zo = 90Ω	
V_{CCIO}	Output Driver Supply (+/– 5%)	2.50	2.50	V
Z_{OUT}	Driver Impedance	10.00	10.00	Ω
R_S	Driver Series Resistor (+/– 1%)	90.00	90.00	Ω
R_{TL}	Driver Parallel Resistor (+/– 1%)	45.00	90.00	Ω
R_{TR}	Receiver Termination (+/– 1%)	45.00	90.00	Ω
V_{OH}	Output High Voltage	1.38	1.48	V
V_{OL}	Output Low Voltage	1.12	1.02	V
V_{OD}	Output Differential Voltage	0.25	0.46	V
V_{CM}	Output Common Mode Voltage	1.25	1.25	V
I_{DC}	DC Output Current	11.24	10.20	mA

1. For input buffer, see LVDS table.

LVPECL33

The LatticeECP3 devices support the differential LVPECL standard. This standard is emulated using complementary LVCMOS outputs in conjunction with a parallel resistor across the driver outputs. The LVPECL input standard is supported by the LVDS differential input buffer. The scheme shown in Figure 3-3 is one possible solution for point-to-point signals.

Figure 3-3. Differential LVPECL33

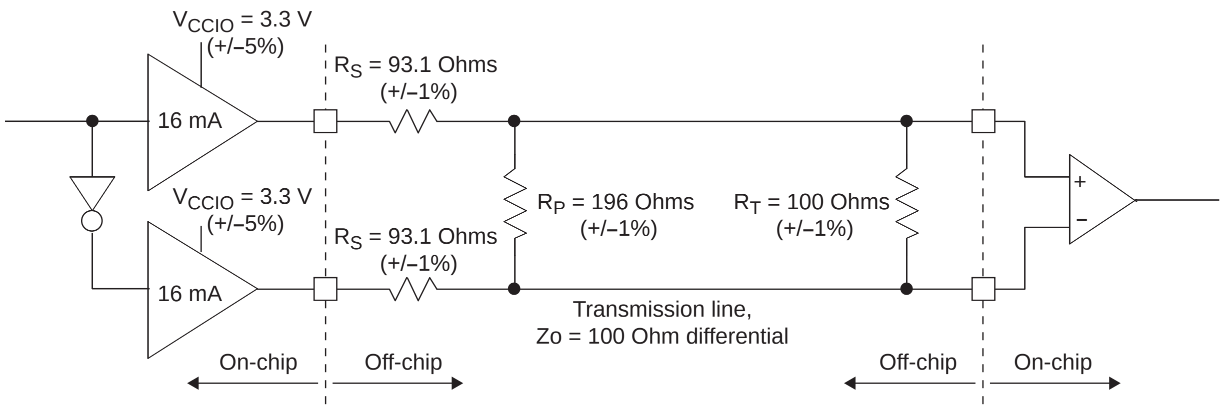


Table 3-3. LVPECL33 DC Conditions[1]

Over Recommended Operating Conditions

Parameter	Description	Typical	Units
V_{CCIO}	Output Driver Supply (+/–5%)	3.30	V
Z_{OUT}	Driver Impedance	10	Ω
R_S	Driver Series Resistor (+/–1%)	93	Ω
R_P	Driver Parallel Resistor (+/–1%)	196	Ω
R_T	Receiver Termination (+/–1%)	100	Ω
V_{OH}	Output High Voltage	2.05	V
V_{OL}	Output Low Voltage	1.25	V
V_{OD}	Output Differential Voltage	0.80	V
V_{CM}	Output Common Mode Voltage	1.65	V
Z_{BACK}	Back Impedance	100.5	Ω
I_{DC}	DC Output Current	12.11	mA

1. For input buffer, see LVDS table.

LatticeECP3 External Switching Characteristics (Continued)[1, 2, 3, 13]

Over Recommended Commercial Operating Conditions

Parameter	Description	Device	–8		–7		–6		Units
			Min.	Max.	Min.	Max.	Min.	Max.	
Generic DDRX2 Inputs with Clock and Data (>10bits wide) are Aligned at Pin (GDDRX2_RX.ECLK.Aligned) (No CLKDIV)									
Left and Right Sides Using DLLCLKPIN for Clock Input									
$t_{DVACLKGDDR}$	Data Setup Before CLK	ECP3-150EA	—	0.225	—	0.225	—	0.225	UI
$t_{DVECLKGDDR}$	Data Hold After CLK	ECP3-150EA	0.775	—	0.775	—	0.775	—	UI
f_{MAX_GDDR}	DDRX2 Clock Frequency	ECP3-150EA	—	460	—	385	—	345	MHz
$t_{DVACLKGDDR}$	Data Setup Before CLK	ECP3-70EA/95EA	—	0.225	—	0.225	—	0.225	UI
$t_{DVECLKGDDR}$	Data Hold After CLK	ECP3-70EA/95EA	0.775	—	0.775	—	0.775	—	UI
fMAX_GDDR	DDRX2 Clock Frequency	ECP3-70EA/95EA	—	460	—	385	—	311	MHz
$t_{DVACLKGDDR}$	Data Setup Before CLK	ECP3-35EA	—	0.210	—	0.210	—	0.210	UI
$t_{DVECLKGDDR}$	Data Hold After CLK	ECP3-35EA	0.790	—	0.790	—	0.790	—	UI
f_{MAX_GDDR}	DDRX2 Clock Frequency	ECP3-35EA	—	460	—	385	—	311	MHz
$t_{DVACLKGDDR}$	Data Setup Before CLK (Left and Right Sides)	ECP3-17EA	—	0.210	—	0.210	—	0.210	UI
$t_{DVECLKGDDR}$	Data Hold After CLK	ECP3-17EA	0.790	—	0.790	—	0.790	—	UI
f_{MAX_GDDR}	DDRX2 Clock Frequency	ECP3-17EA	—	460	—	385	—	311	MHz
Top Side Using PCLK Pin for Clock Input									
$t_{DVACLKGDDR}$	Data Setup Before CLK	ECP3-150EA	—	0.225	—	0.225	—	0.225	UI
$t_{DVECLKGDDR}$	Data Hold After CLK	ECP3-150EA	0.775	—	0.775	—	0.775	—	UI
f_{MAX_GDDR}	DDRX2 Clock Frequency	ECP3-150EA	—	235	—	170	—	130	MHz
$t_{DVACLKGDDR}$	Data Setup Before CLK	ECP3-70EA/95EA	—	0.225	—	0.225	—	0.225	UI
$t_{DVECLKGDDR}$	Data Hold After CLK	ECP3-70EA/95EA	0.775	—	0.775	—	0.775	—	UI
f_{MAX_GDDR}	DDRX2 Clock Frequency	ECP3-70EA/95EA	—	235	—	170	—	130	MHz
$t_{DVACLKGDDR}$	Data Setup Before CLK	ECP3-35EA	—	0.210	—	0.210	—	0.210	UI
$t_{DVECLKGDDR}$	Data Hold After CLK	ECP3-35EA	0.790	—	0.790	—	0.790	—	UI
f_{MAX_GDDR}	DDRX2 Clock Frequency	ECP3-35EA	—	235	—	170	—	130	MHz
$t_{DVACLKGDDR}$	Data Setup Before CLK	ECP3-17EA	—	0.210	—	0.210	—	0.210	UI
$t_{DVECLKGDDR}$	Data Hold After CLK	ECP3-17EA	0.790	—	0.790	—	0.790	—	UI
f_{MAX_GDDR}	DDRX2 Clock Frequency	ECP3-17EA	—	235	—	170	—	130	MHz
Generic DDRX2 Inputs with Clock and Data (<10 Bits Wide) Centered at Pin (GDDRX2_RX.DQS.Centered) Using DQS Pin for Clock Input									
Left and Right Sides									
t_{SUGDDR}	Data Setup Before CLK	All ECP3EA Devices	330	—	330	—	352	—	ps
t_{HOGDDR}	Data Hold After CLK	All ECP3EA Devices	330	—	330	—	352	—	ps
f_{MAX_GDDR}	DDRX2 Clock Frequency	All ECP3EA Devices	—	400	—	400	—	375	MHz
Generic DDRX2 Inputs with Clock and Data (<10 Bits Wide) Aligned at Pin (GDDRX2_RX.DQS.Aligned) Using DQS Pin for Clock Input									
Left and Right Sides									
$t_{DVACLKGDDR}$	Data Setup Before CLK	All ECP3EA Devices	—	0.225	—	0.225	—	0.225	UI
$t_{DVECLKGDDR}$	Data Hold After CLK	All ECP3EA Devices	0.775	—	0.775	—	0.775	—	UI
f_{MAX_GDDR}	DDRX2 Clock Frequency	All ECP3EA Devices	—	400	—	400	—	375	MHz
Generic DDRX1 Output with Clock and Data (>10 Bits Wide) Centered at Pin (GDDRX1_TX.SCLK.Centered)[10]									
$t_{DVBGDDR}$	Data Valid Before CLK	ECP3-150EA	670	—	670	—	670	—	ps
$t_{DVAGDDR}$	Data Valid After CLK	ECP3-150EA	670	—	670	—	670	—	ps
f_{MAX_GDDR}	DDRX1 Clock Frequency	ECP3-150EA	—	250	—	250	—	250	MHz
$t_{DVBGDDR}$	Data Valid Before CLK	ECP3-70EA/95EA	666	—	665	—	664	—	ps
$t_{DVAGDDR}$	Data Valid After CLK	ECP3-70EA/95EA	666	—	665	—	664	—	ps

LatticeECP3 Internal Switching Characteristics[1, 2, 5] (Continued)

Over Recommended Commercial Operating Conditions

Parameter	Description	–8		–7		–6		Units.
		Min.	Max.	Min.	Max.	Min.	Max.	
t_{HWREN_EBR}	Hold Write/Read Enable to EBR Memory	0.141	—	0.145	—	0.149	—	ns
t_{SUCE_EBR}	Clock Enable Setup Time to EBR Output Register	0.087	—	0.096	—	0.104	—	ns
t_{HCE_EBR}	Clock Enable Hold Time to EBR Output Register	–0.066	—	–0.080	—	–0.094	—	ns
t_{SUBE_EBR}	Byte Enable Set-Up Time to EBR Output Register	–0.071	—	–0.070	—	–0.068	—	ns
t_{HBE_EBR}	Byte Enable Hold Time to EBR Output Register	0.118	—	0.098	—	0.077	—	ns
DSP Block Timing[3]								
t_{SUI_DSP}	Input Register Setup Time	0.32	—	0.36	—	0.39	—	ns
t_{HI_DSP}	Input Register Hold Time	–0.17	—	–0.19	—	–0.21	—	ns
t_{SUP_DSP}	Pipeline Register Setup Time	2.23	—	2.30	—	2.37	—	ns
t_{HP_DSP}	Pipeline Register Hold Time	–1.02	—	–1.09	—	–1.15	—	ns
t_{SUO_DSP}	Output Register Setup Time	3.09	—	3.22	—	3.34	—	ns
t_{HO_DSP}	Output Register Hold Time	–1.67	—	–1.76	—	–1.84	—	ns
t_{COI_DSP}	Input Register Clock to Output Time	—	3.05	—	3.35	—	3.73	ns
t_{COP_DSP}	Pipeline Register Clock to Output Time	—	1.30	—	1.47	—	1.64	ns
t_{COO_DSP}	Output Register Clock to Output Time	—	0.58	—	0.60	—	0.62	ns
t_{SUOPT_DSP}	Opcode Register Setup Time	0.31	—	0.35	—	0.39	—	ns
t_{HOPT_DSP}	Opcode Register Hold Time	–0.20	—	–0.24	—	–0.27	—	ns
t_{SUDATA_DSP}	Cascade_data through ALU to Output Register Setup Time	1.69	—	1.94	—	2.14	—	ns
t_{HPDATA_DSP}	Cascade_data through ALU to Output Register Hold Time	–0.58	—	–0.80	—	–0.97	—	ns

1. Internal parameters are characterized but not tested on every device.
2. Commercial timing numbers are shown. Industrial timing numbers are typically slower and can be extracted from the Diamond or ispLEVER software.
3. DSP slice is configured in Multiply Add/Sub 18 x 18 mode.
4. The output register is in Flip-flop mode.
5. For details on –9 speed grade devices, please contact your Lattice Sales Representative.

sysCLOCK PLL Timing

Over Recommended Operating Conditions

Parameter	Descriptions	Conditions	Clock	Min.	Typ.	Max.	Units
f_{IN}	Input clock frequency (CLKI, CLKFB)		Edge clock	2	—	500	MHz
			Primary clock[4]	2	—	420	MHz
f_{OUT}	Output clock frequency (CLKOP, CLKOS)		Edge clock	4	—	500	MHz
			Primary clock[4]	4	—	420	MHz
f_{OUT1}	K-Divider output frequency	CLKOK		0.03125	—	250	MHz
f_{OUT2}	K2-Divider output frequency	CLKOK2		0.667	—	166	MHz
f_{VCO}	PLL VCO frequency			500	—	1000	MHz
f_{PFD}[3]	Phase detector input frequency		Edge clock	2	—	500	MHz
			Primary clock[4]	2	—	420	MHz
AC Characteristics							
t_{PA}	Programmable delay unit			65	130	260	ps
t_{DT}	Output clock duty cycle (CLKOS, at 50% setting)		Edge clock	45	50	55	%
		$f_{OUT} \leq 250$ MHz	Primary clock	45	50	55	%
		$f_{OUT} > 250$ MHz	Primary clock	30	50	70	%
t_{CPA}	Coarse phase shift error (CLKOS, at all settings)			-5	0	+5	% of period
t_{OPW}	Output clock pulse width high or low (CLKOS)			1.8	—	—	ns
t_{OPJIT}[1]	Output clock period jitter	$f_{OUT} \geq 420$ MHz		—	—	200	ps
		420 MHz > $f_{OUT} \geq 100$ MHz		—	—	250	ps
		$f_{OUT} < 100$ MHz		—	—	0.025	UIPP
t_{SK}	Input clock to output clock skew when N/M = integer			—	—	500	ps
t_{LOCK}[2]	Lock time	2 to 25 MHz		—	—	200	us
		25 to 500 MHz		—	—	50	us
t_{UNLOCK}	Reset to PLL unlock time to ensure fast reset			—	—	50	ns
t_{HI}	Input clock high time	90% to 90%		0.5	—	—	ns
t_{LO}	Input clock low time	10% to 10%		0.5	—	—	ns
t_{IPJIT}	Input clock period jitter			—	—	400	ps
t_{RST}	Reset signal pulse width high, RSTK			10	—	—	ns
	Reset signal pulse width high, RST			500	—	—	ns

1. Jitter sample is taken over 10,000 samples of the primary PLL output with clean reference clock with no additional I/O toggling.
2. Output clock is valid after t_{LOCK} for PLL reset and dynamic delay adjustment.
3. Period jitter and cycle-to-cycle jitter numbers are guaranteed for f_{PFD} > 4 MHz. For f_{PFD} < 4 MHz, the jitter numbers may not be met in certain conditions. Please contact the factory for f_{PFD} < 4 MHz.
4. When using internal feedback, maximum can be up to 500 MHz.

Figure 3-14. Jitter Transfer – 3.125 Gbps

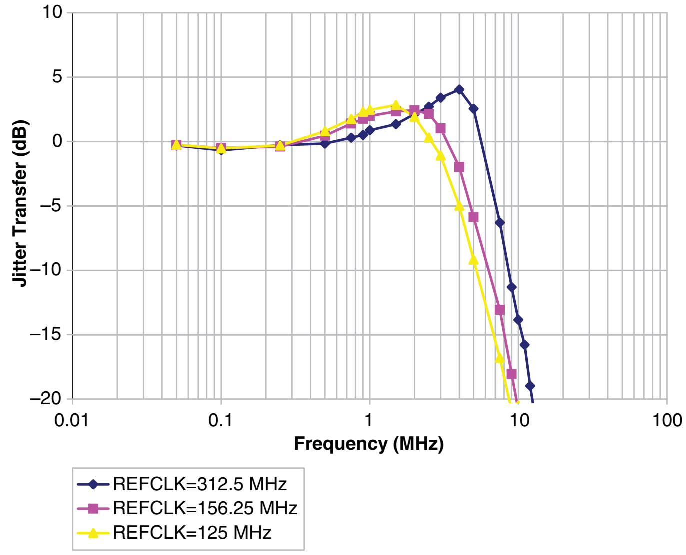


Figure 3-15. Jitter Transfer – 2.5 Gbps

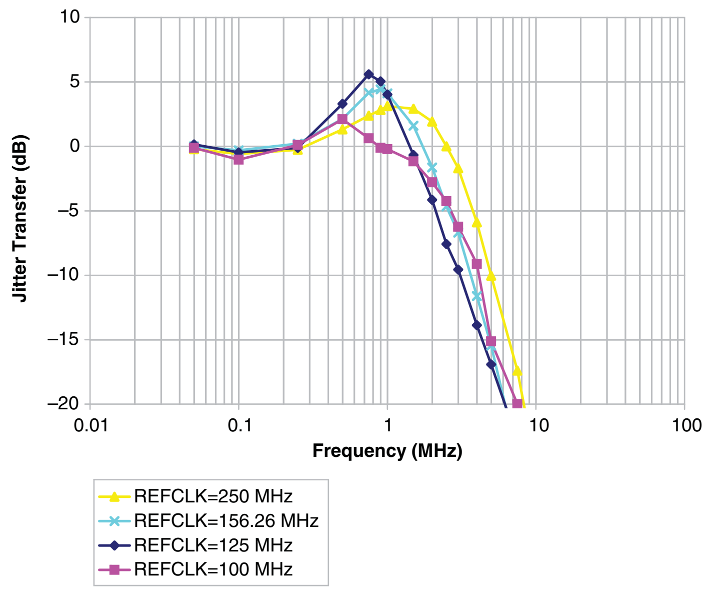
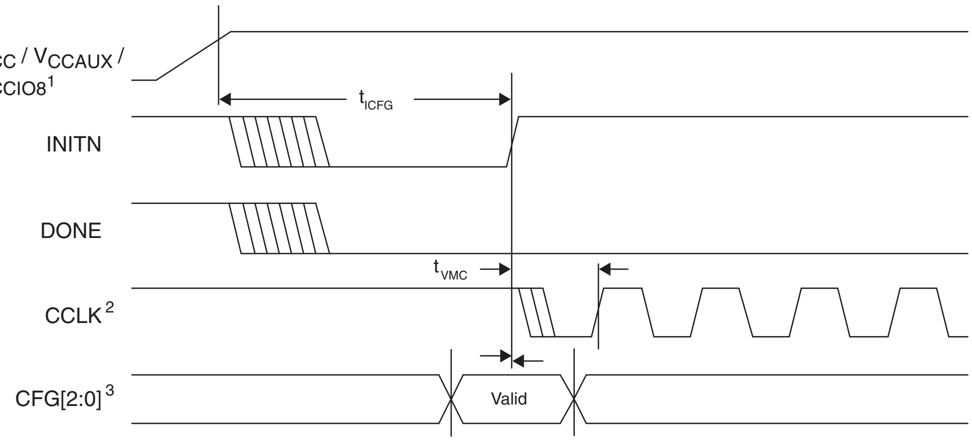


Figure 3-24. Power-On-Reset (POR) Timing



1. Time taken from V_{CC}, V_{CCAUX} or V_{CCIO8}, whichever is the last to cross the POR trip point.
2. Device is in a Master Mode (SPI, SPIm).
3. The CFG pins are normally static (hard wired).

Figure 3-25. sysCONFIG Port Timing

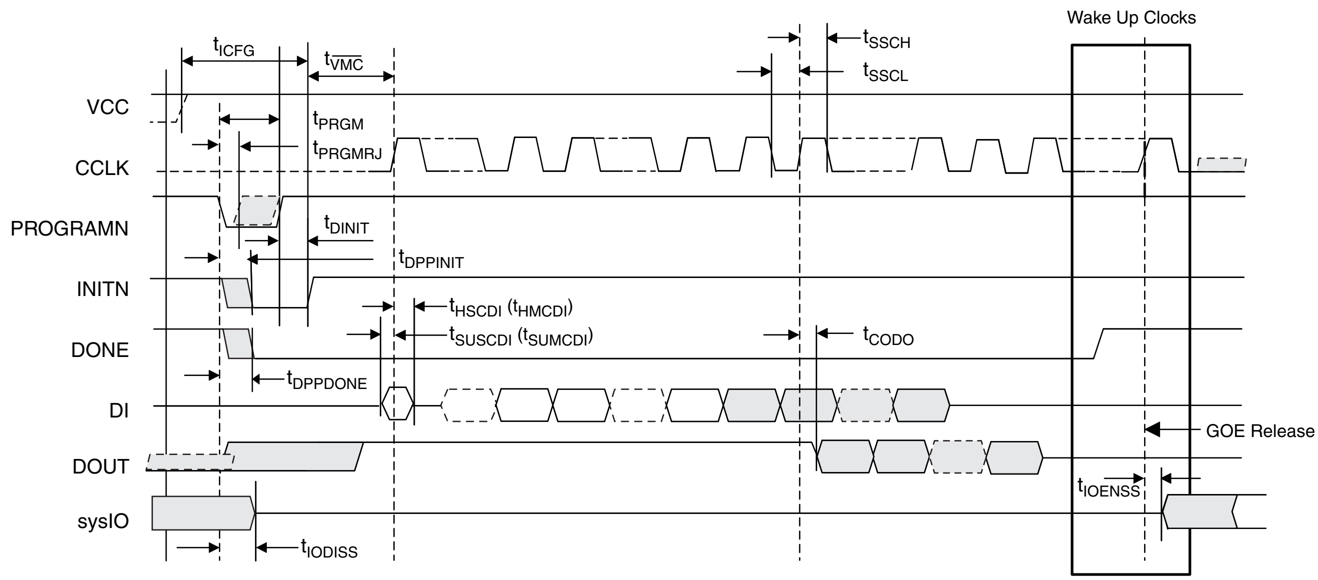
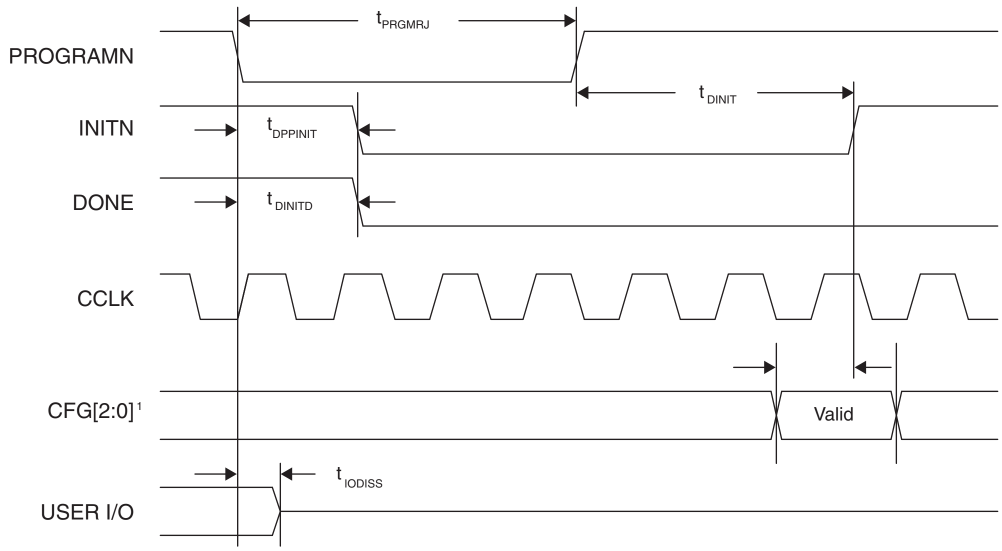


Figure 3-26. Configuration from PROGRAMN Timing



1. The CFG pins are normally static (hard wired)

Figure 3-27. Wake-Up Timing

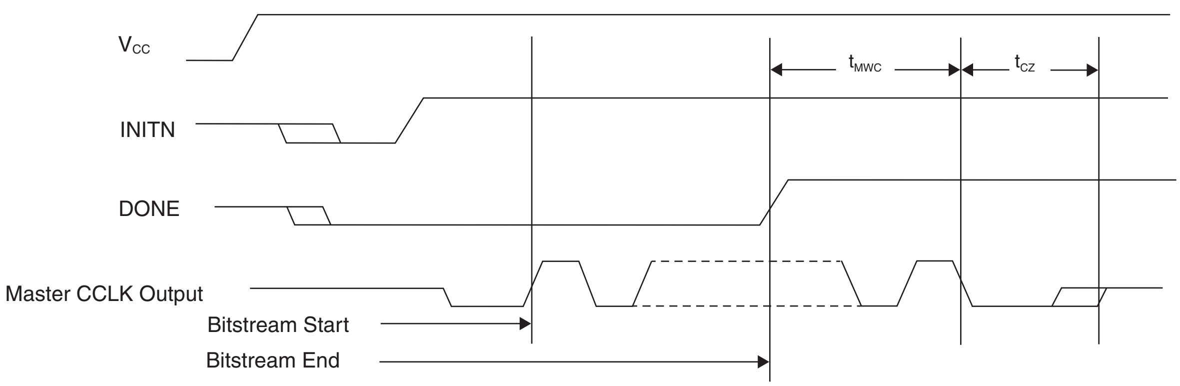


Figure 3-28. Master SPI Configuration Waveforms

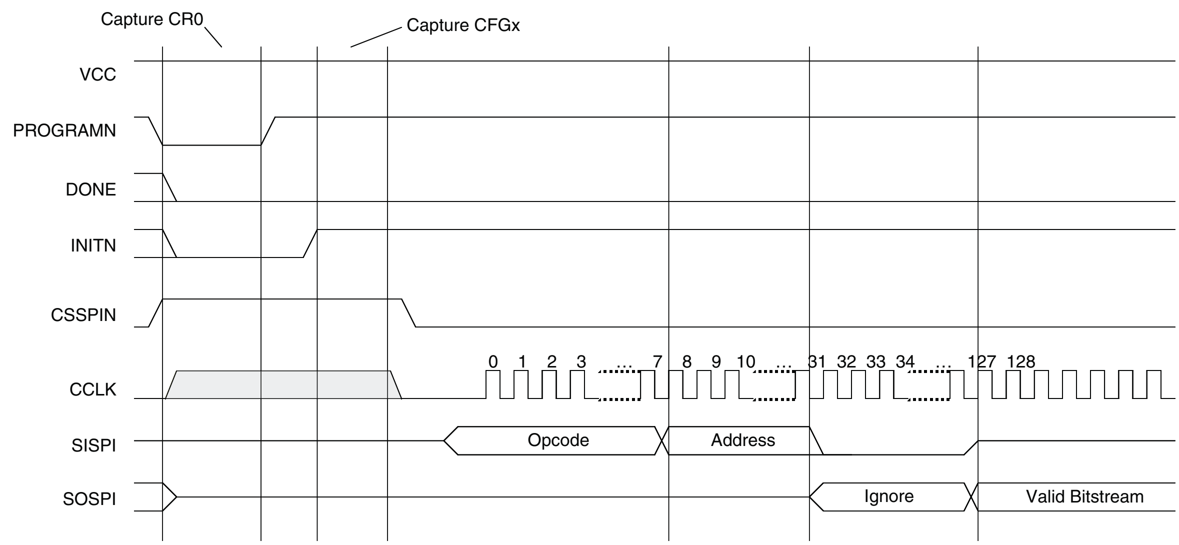
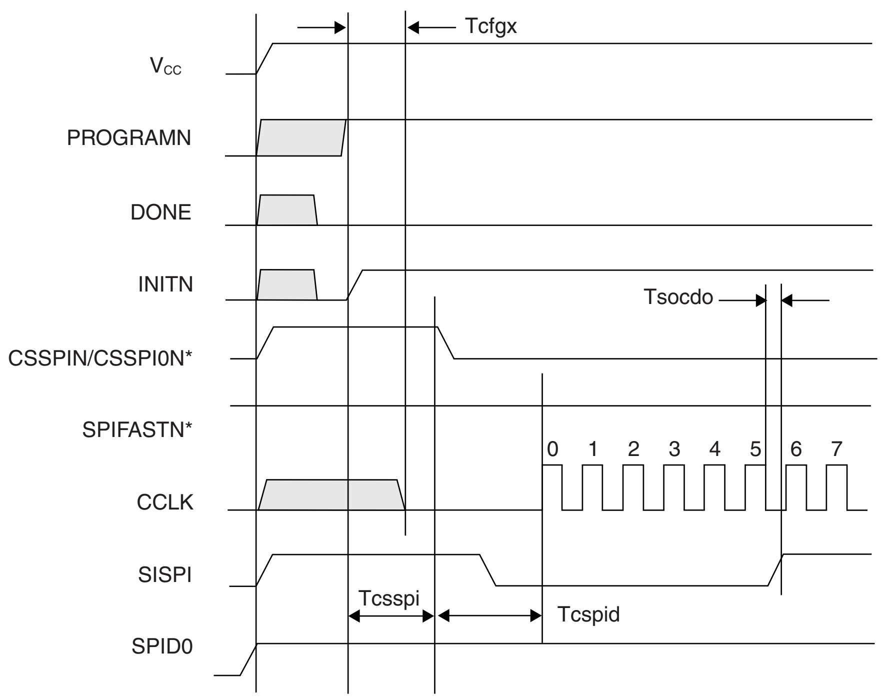


Figure 3-29. Master SPI POR Waveforms



Pin Information Summary (Cont.)

Pin Information Summary		ECP3-95EA			ECP3-150EA	
Pin Type		484 fpBGA	672 fpBGA	1156 fpBGA	672 fpBGA	1156 fpBGA
General Purpose Inputs/Outputs per bank	Bank 0	42	60	86	60	94
	Bank 1	36	48	78	48	86
	Bank 2	24	34	36	34	58
	Bank 3	54	59	86	59	104
	Bank 6	63	67	86	67	104
	Bank 7	36	48	54	48	76
	Bank 8	24	24	24	24	24
General Purpose Inputs per Bank	Bank 0	0	0	0	0	0
	Bank 1	0	0	0	0	0
	Bank 2	4	8	8	8	8
	Bank 3	4	12	12	12	12
	Bank 6	4	12	12	12	12
	Bank 7	4	8	8	8	8
	Bank 8	0	0	0	0	0
General Purpose Outputs per Bank	Bank 0	0	0	0	0	0
	Bank 1	0	0	0	0	0
	Bank 2	0	0	0	0	0
	Bank 3	0	0	0	0	0
	Bank 6	0	0	0	0	0
	Bank 7	0	0	0	0	0
	Bank 8	0	0	0	0	0
Total Single-Ended User I/O		295	380	490	380	586
VCC		16	32	32	32	32
VCCAUX		8	12	16	12	16
VTT		4	4	8	4	8
VCCA		4	8	16	8	16
VCCPLL		4	4	4	4	4
VCCIO	Bank 0	2	4	4	4	4
	Bank 1	2	4	4	4	4
	Bank 2	2	4	4	4	4
	Bank 3	2	4	4	4	4
	Bank 6	2	4	4	4	4
	Bank 7	2	4	4	4	4
	Bank 8	2	2	2	2	2
VCCJ		1	1	1	1	1
TAP		4	4	4	4	4
GND, GNDIO		98	139	233	139	233
NC		0	0	238	0	116
Reserved[1]		2	2	2	2	2
SERDES		26	52	78	52	104
Miscellaneous Pins		8	8	8	8	8
Total Bonded Pins		484	672	1156	672	1156

Pin Information Summary (Cont.)

Pin Information Summary		ECP3-95EA			ECP3-150EA	
Pin Type		484 fpBGA	672 fpBGA	1156 fpBGA	672 fpBGA	1156 fpBGA
Emulated Differential I/O per Bank	Bank 0	21	30	43	30	47
	Bank 1	18	24	39	24	43
	Bank 2	8	12	13	12	18
	Bank 3	20	23	33	23	37
	Bank 6	22	25	33	25	37
	Bank 7	11	16	18	16	24
	Bank 8	12	12	12	12	12
Highspeed Differential I/O per Bank	Bank 0	0	0	0	0	0
	Bank 1	0	0	0	0	0
	Bank 2	6	9	9	9	15
	Bank 3	9	12	16	12	21
	Bank 6	11	14	16	14	21
	Bank 7	9	12	13	12	18
	Bank 8	0	0	0	0	0
Total Single Ended/ Total Differential I/O per Bank	Bank 0	42/21	60/30	86/43	60/30	94/47
	Bank 1	36/18	48/24	78/39	48/24	86/43
	Bank 2	28/14	42/21	44/22	42/21	66/33
	Bank 3	58/29	71/35	98/49	71/35	116/58
	Bank 6	67/33	78/39	98/49	78/39	116/58
	Bank 7	40/20	56/28	62/31	56/28	84/42
	Bank 8	24/12	24/12	24/12	24/12	24/12
DDR Groups Bonded per Bank	Bank 0	3	5	7	5	7
	Bank 1	3	4	7	4	7
	Bank 2	2	3	3	3	4
	Bank 3	3	4	5	4	7
	Bank 6	4	4	5	4	7
	Bank 7	3	4	4	4	6
	Configuration Bank8	0	0	0	0	0
SERDES Quads		1	2	3	2	4

1.These pins must remain floating on the board.

Package Pinout Information

Package pinout information can be found under “Data Sheets” on the LatticeECP3 product pages on the Lattice website at http://www.latticesemi.com/Products/FPGAandCPLD/LatticeECP3 and in the Diamond or ispLEVER software tools. To create pinout information from within ispLEVER Design Planner, select **Tools > Spreadsheet View**. Then select **Select File > Export** and choose a type of output file. To create a pin information file from within Diamond select **Tools > Spreadsheet View** or **Tools >Package View**; then, select **File > Export** and choose a type of output file. See Diamond or ispLEVER Help for more information.

Thermal Management

Thermal management is recommended as part of any sound FPGA design methodology. To assess the thermal characteristics of a system, Lattice specifies a maximum allowable junction temperature in all device data sheets. Designers must complete a thermal analysis of their specific design to ensure that the device and package do not exceed the junction temperature limits. Refer to the Thermal Management document to find the device/package specific thermal values.

For Further Information

For further information regarding Thermal Management, refer to the following:

- Thermal Management document
- TN1181, Power Consumption and Management for LatticeECP3 Devices
- Power Calculator tool included with the Diamond and ispLEVER design tools, or as a standalone download from www.latticesemi.com/software

Part Number	Voltage	Grade[1]	Power	Package	Pins	Temp.	LUTs (K)
LFE3-70EA-6FN484C	1.2 V	–6	STD	Lead-Free fpBGA	484	COM	67
LFE3-70EA-7FN484C	1.2 V	–7	STD	Lead-Free fpBGA	484	COM	67
LFE3-70EA-8FN484C	1.2 V	–8	STD	Lead-Free fpBGA	484	COM	67
LFE3-70EA-6LFN484C	1.2 V	–6	LOW	Lead-Free fpBGA	484	COM	67
LFE3-70EA-7LFN484C	1.2 V	–7	LOW	Lead-Free fpBGA	484	COM	67
LFE3-70EA-8LFN484C	1.2 V	–8	LOW	Lead-Free fpBGA	484	COM	67
LFE3-70EA-6FN672C	1.2 V	–6	STD	Lead-Free fpBGA	672	COM	67
LFE3-70EA-7FN672C	1.2 V	–7	STD	Lead-Free fpBGA	672	COM	67
LFE3-70EA-8FN672C	1.2 V	–8	STD	Lead-Free fpBGA	672	COM	67
LFE3-70EA-6LFN672C	1.2 V	–6	LOW	Lead-Free fpBGA	672	COM	67
LFE3-70EA-7LFN672C	1.2 V	–7	LOW	Lead-Free fpBGA	672	COM	67
LFE3-70EA-8LFN672C	1.2 V	–8	LOW	Lead-Free fpBGA	672	COM	67
LFE3-70EA-6FN1156C	1.2 V	–6	STD	Lead-Free fpBGA	1156	COM	67
LFE3-70EA-7FN1156C	1.2 V	–7	STD	Lead-Free fpBGA	1156	COM	67
LFE3-70EA-8FN1156C	1.2 V	–8	STD	Lead-Free fpBGA	1156	COM	67
LFE3-70EA-6LFN1156C	1.2 V	–6	LOW	Lead-Free fpBGA	1156	COM	67
LFE3-70EA-7LFN1156C	1.2 V	–7	LOW	Lead-Free fpBGA	1156	COM	67
LFE3-70EA-8LFN1156C	1.2 V	–8	LOW	Lead-Free fpBGA	1156	COM	67

1. For ordering information on -9 speed grade devices, please contact your Lattice Sales Representative.

Part Number	Voltage	Grade[1]	Power	Package	Pins	Temp.	LUTs (K)
LFE3-95EA-6FN484C	1.2 V	–6	STD	Lead-Free fpBGA	484	COM	92
LFE3-95EA-7FN484C	1.2 V	–7	STD	Lead-Free fpBGA	484	COM	92
LFE3-95EA-8FN484C	1.2 V	–8	STD	Lead-Free fpBGA	484	COM	92
LFE3-95EA-6LFN484C	1.2 V	–6	LOW	Lead-Free fpBGA	484	COM	92
LFE3-95EA-7LFN484C	1.2 V	–7	LOW	Lead-Free fpBGA	484	COM	92
LFE3-95EA-8LFN484C	1.2 V	–8	LOW	Lead-Free fpBGA	484	COM	92
LFE3-95EA-6FN672C	1.2 V	–6	STD	Lead-Free fpBGA	672	COM	92
LFE3-95EA-7FN672C	1.2 V	–7	STD	Lead-Free fpBGA	672	COM	92
LFE3-95EA-8FN672C	1.2 V	–8	STD	Lead-Free fpBGA	672	COM	92
LFE3-95EA-6LFN672C	1.2 V	–6	LOW	Lead-Free fpBGA	672	COM	92
LFE3-95EA-7LFN672C	1.2 V	–7	LOW	Lead-Free fpBGA	672	COM	92
LFE3-95EA-8LFN672C	1.2 V	–8	LOW	Lead-Free fpBGA	672	COM	92
LFE3-95EA-6FN1156C	1.2 V	–6	STD	Lead-Free fpBGA	1156	COM	92
LFE3-95EA-7FN1156C	1.2 V	–7	STD	Lead-Free fpBGA	1156	COM	92
LFE3-95EA-8FN1156C	1.2 V	–8	STD	Lead-Free fpBGA	1156	COM	92
LFE3-95EA-6LFN1156C	1.2 V	–6	LOW	Lead-Free fpBGA	1156	COM	92
LFE3-95EA-7LFN1156C	1.2 V	–7	LOW	Lead-Free fpBGA	1156	COM	92
LFE3-95EA-8LFN1156C	1.2 V	–8	LOW	Lead-Free fpBGA	1156	COM	92

1. For ordering information on -9 speed grade devices, please contact your Lattice Sales Representative.

LatticeECP3 Family Data Sheet Revision History

March 2015 **Data Sheet DS1021**

Date	Version	Section	Change Summary
March 2015	2.8EA	Pinout Information	Updated Package Pinout Information section. Changed reference to http://www.latticesemi.com/Products/FPGAandCPLD/LatticeECP3.
		All	Minor style/formatting changes.
April 2014	02.7EA	DC and Switching Characteristics	Updated LatticeECP3 Supply Current (Standby) table power numbers.
			Removed speed grade -9 timing numbers in the following sections: — Typical Building Block Function Performance — LatticeECP3 External Switching Characteristics — LatticeECP3 Internal Switching Characteristics — LatticeECP3 Family Timing Adders
		Ordering Information	Removed ordering information for -9 speed grade devices.
March 2014	02.6EA	DC and Switching Characteristics	Added information to the sysI/O Single-Ended DC Electrical Characteristics section footnote.
February 2014	02.5EA	DC and Switching Characteristics	Updated Hot Socketing Specifications table. Changed I_{PW} to I_{PD} in footnote 3.
			Updated the following figures: — Figure 3-25, sysCONFIG Port Timing — Figure 3-27, Wake-Up Timing
		Supplemental Information	Added technical note references.
September 2013	02.4EA	DC and Switching Characteristics	Updated the Wake-Up Timing Diagram
			Added the following figures: — Master SPI POR Waveforms — SPI Configuration Waveforms — Slave SPI HOLDN Waveforms
			Added tIODISS and tIOENSS parameters in LatticeECP3 sysCONFIG Port Timing Specifications table.
June 2013	02.3EA	Architecture	sysI/O Buffer Banks text section – Updated description of "Top (Bank 0 and Bank 1) and Bottom sysIO Buffer Pairs (Single-Ended Outputs Only)" for hot socketing information.
			sysI/O Buffer Banks text section – Updated description of "Configuration Bank sysI/O Buffer Pairs (Single-Ended Outputs, Only on Shared Pins When Not Used by Configuration)" for PCI clamp information.
			On-Chip Oscillator section – clarified the speed of the internal CMOS oscillator (130 MHz +/- 15%).
			Architecture Overview section – Added information on the state of the register on power up and after configuration.
		DC and Switching Characteristics	sysI/O Recommended Operating Conditions table – Removed reference to footnote 1 from RSDS standard.
			sysI/O Single-Ended DC Electrical Characteristics table – Modified footnote 1.
			Added Oscillator Output Frequency table.
			LatticeECP3 sysCONFIG Port Timing Specifications table – Updated min. column for t_{CODO} parameter.
			LatticeECP3 Family Timing Adders table – Description column, references to VCCIO = 3.0V changed to 3.3V. For PPLVDS, description changed from emulated to True LVDS and VCCIO = 2.5V changed to VCCIO = 2.5V or 3.3V.

© 2015 Lattice Semiconductor Corp. All Lattice trademarks, registered trademarks, patents, and disclaimers are as listed at www.latticesemi.com/legal. All other brand or product names are trademarks or registered trademarks of their respective holders. The specifications and information herein are subject to change without notice.